

note 1 B1

1. (Twice Amended) A method of forming a fine pattern, comprising the steps of:
forming a silicon-oxide-based film over a substrate, wherein the silicon-oxide-based film is formed at a temperature of 500°C or more by means of a plasma CVD technique;
forming a chemically-amplified photoresist layer on the silicon-oxide-based film;
and
transferring a mask pattern onto the chemically-amplified photoresist layer upon exposure through a mask; wherein, in the step of forming the silicon-oxide-based film, a nitrogen content of the surface of the silicon-oxide-based film is made to about a value of 0.1 atm.% or less.

note 2 B2

5. (Twice Amended) A method of manufacturing a semiconductor device, comprising the steps of:
forming a silicon-oxide-based film over an underlying layer, wherein the silicon-oxide-based film is formed at a temperature of 500°C or more by means of a plasma CVD technique such that a surface of the silicon-oxide-based film has a nitrogen content of 0.1 atm. % or less;
forming a chemically-amplified photoresist layer on the silicon-oxide-based film;
transferring a mask pattern onto the chemically-amplified photoresist layer upon exposure through a mask; and
etching the underlying layer by way of a resist pattern, to thereby form a fine pattern in the underlying layer.